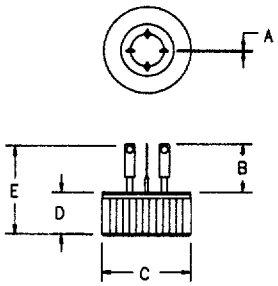
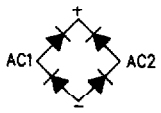
Single Phase Bridge Modules
MT200 – MT800





Dim.	Inches		Millimeter		
	Minimum	Maximum	Minimum	Maximum	Notes
A	.020	.030	.508	.762	
B	.350	.370	8.89	9.40	
C	.745	.760	18.92	19.30	Dia.
D	.405	.420	10.29	10.67	
E	.775	.795	19.68	20.19	

E

Microsemi Catalog Number	Repetitive Peak Reverse Voltage
MT200*	200V
MT400*	400V
MT600*	600V
MT800*	800V

*Available with TO3 mounting flange
For other circuit configurations, consult factory

- Glass Passivated Die
- Glass to metal construction
- Single phase rectification
- Available to 800 Volts
- Cup electrically isolated from terminals

Electrical Characteristics

Maximum DC output current, single phase	I_O	25 Amps	Sine wave, 180° conduction
Maximum case temperature	T_C	137°C	
Maximum surge current per diode	I_{FSM}	250 Amps	8.3ms, half sine, T_J = 175°C
Max I^2t for fusing	I^2t	260 A^2s	
Max peak forward voltage per diode	V_{FM}	1.2 Volts	@ Io; T_J = 25°C*
Max peak reverse current per diode	I_{RM}	1.0 mA	V_{RRM}, T_J = 150°C
Minimum isolation voltage	V_{ISOL}	2500 V_{RMS}	any terminal to case

*Pulse test: Pulse width 300 μsec, Duty cycle 2%

Thermal and Mechanical Characteristics

Storage temperature range	T_{STG}	−65°C to 200°C
Operating junction temperature range	T_J	−65°C to 200°C
Maximum thermal resistance per diode	$R_{\theta JC}$	2.0°C/W Junction to Lead
Typical thermal resistance	$R_{\theta CS}$	0.2°C/W Case to sink
Weight		0.53 ounces (15.0 grams) typical

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Microsemi Corp.
Colorado

MT200 – MT800

Figure 1
Typical Forward Characteristics – Per Diode

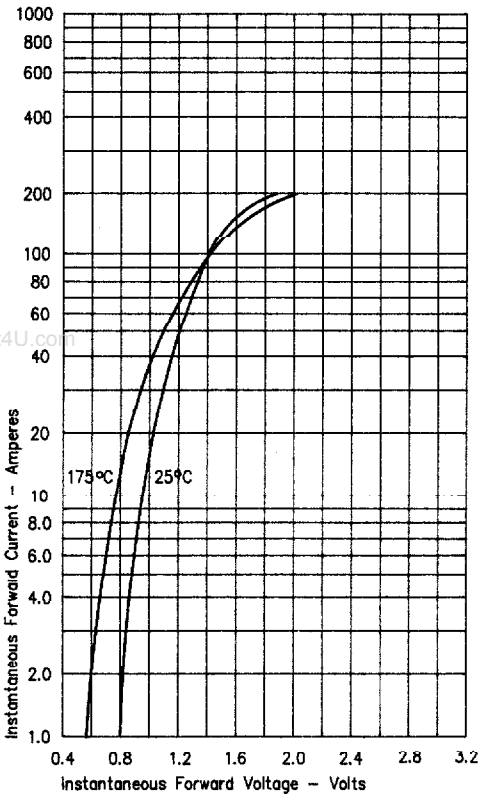

Figure 2
Forward Current Derating – Per Diode

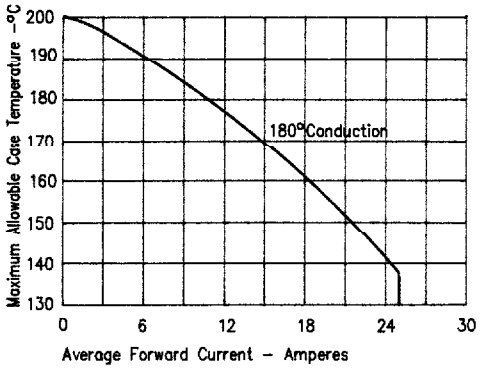

Figure 3
Maximum Nonrepetitive Surge Current – Per Diode